

[Notes]

1. The inventions described in claims 1 to 11 of the Scope of the Patent Claims of this application pertain to a method for the manufacture of an active matrix substrate comprising, for example, a laminated film laminated level and a resist etching level and, by virtue of the fact that, in a comparison of the inventions of this application with a technique such as a method for the manufacture of a matrix substrate comprising a step for the laminating of an insulating layer and a semiconductor layer as described in Korean Registered Patent Application No. 0170452 (hereafter referred to as cited document 1, 1999.03.20) and the technical details pertaining to the method for the manufacture of an active matrix substrate comprising a step for pattern formation in a single PR process of films on mutually different layers as described in Japanese Unexamined Patent Application No. Heisei 12-66240 (hereafter referred to as cited document 2, 2000.03.03), the objectives, configurations and effects thereof are similar, the inventions of this application, based on the above-noted cited document 1 and 2, are able to be invented easily and without technical configuration difficulties by a person with knowledge common to the field of technology to which this invention belongs. (Patent Act, Article 29, Paragraph 2)

2. In that, for example, a scientifically unclear term "taiseki (accumulate)" is given in the scope of the patent claims of this application and, in addition, an incongruent sentence expression "... comprising a large number of film thicknesses" is given in claim 1, the description given in the Scope of the Patent Claims is unclear. (Patent Act, Article 42, Paragraph 4, Section 2)

[Appendices]

Appendix 1 Korean Registered Patent Application No.

0170452 (1999.03.20)

1x

Appendix 2 Japanese Unexamined Patent Application No.

Heisei 12-66240 (2000.03.03)

1x

2003.09.16